PD - 95090A

International
IOR Rectifier

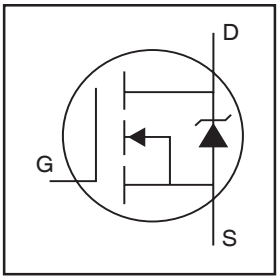
AUTOMOTIVE MOSFET

IRLR3915PbF
IRLU3915PbF

HEXFET® Power MOSFET

Features

- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free



V_{DSS} = 55V

$R_{DS(on)}$ = 14mΩ

I_D = 30A

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this product are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

D-Pak IRLR3915PbF | I-Pak IRLU3915PbF

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Silicon limited)	61	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V (See Fig.9)	43	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Package limited)	30	
I_{DM}	Pulsed Drain Current ①	240	
P_D @T_C = 25°C	Power Dissipation	120	W
	Linear Derating Factor	0.77	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy②	200	mJ
E_{AS} (6 sigma)	Single Pulse Avalanche Energy Tested Value⑦	600	
I_{AR}	Avalanche Current①	See Fig.12a, 12b, 15, 16	A
E_{AR}	Repetitive Avalanche Energy⑥		mJ
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	1.3	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)⑧	——	50	
$R_{\theta JA}$	Junction-to-Ambient——	110		

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

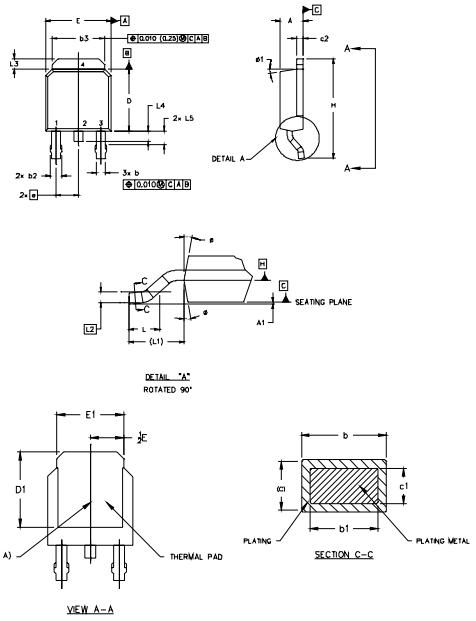
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.057	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	12	14	mΩ	V_{GS} = 10V, I_D = 30A ④
		—	14	17		V_{GS} = 5.0V, I_D = 26A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	V_{DS} = 10V, I_D = 250µA
g_{fs}	Forward Transconductance	42	—	—	S	V_{DS} = 25V, I_D = 30A
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	µA	V_{DS} = 55V, V_{GS} = 0V
		—	—	250		V_{DS} = 55V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	V_{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-200		V_{GS} = -16V
Q_g	Total Gate Charge	—	61	92	nC	I_D = 30A
Q_{gs}	Gate-to-Source Charge	—	9.0	14		V_{DS} = 44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	17	25		V_{GS} = 10V④
$t_{d(on)}$	Turn-On Delay Time	—	7.4	—	ns	V_{DD} = 28V
t_r	Rise Time	—	51	—		I_D = 30A
$t_{d(off)}$	Turn-Off Delay Time	—	83	—		R_G = 8.5Ω
t_f	Fall Time	—	100	—		V_{GS} = 10V ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1870	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	390	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	74	—		f = 1.0MHz, See Fig. 5
C_{oss}	Output Capacitance	—	2380	—		V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz
C_{oss}	Output Capacitance	—	290	—		V_{GS} = 0V, V_{DS} = 44V, f = 1.0MHz
C_{oss} eff.	Effective Output Capacitance ⑤	—	540	—		V_{GS} = 0V, V_{DS} = 0V to 44V

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	61	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	240		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J = 25°C, I_S = 30A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	62	93	ns	T_J = 25°C, I_F = 30A, V_{DD} = 25xjkl V
Q_{rr}	Reverse Recovery Charge	—	110	170	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3.0 LEAD DIMENSION UNCONTROLLED IN L5.
4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.254] FROM THE LEAD TIP.
6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.13		.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	0.031	5
b2	0.78	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.89	.018	.035	5
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 REF.		.108 REF.		
L2	0.064 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	3
ø	0°	10°	0°	10°	
ø1	0°	15°	0°	15°	

LEAD ASSIGNMENTS

HEXFET

1.- GATE
2.- DRAIN
3.- SOURCE
4.- DRAIN

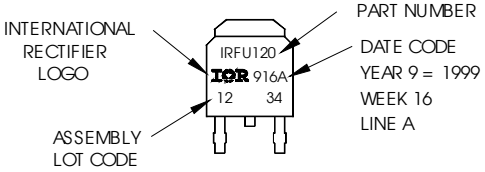
IGBTs, CoPACK

1.- GATE
2.- COLLECTOR
3.- EMITTER
4.- COLLECTOR

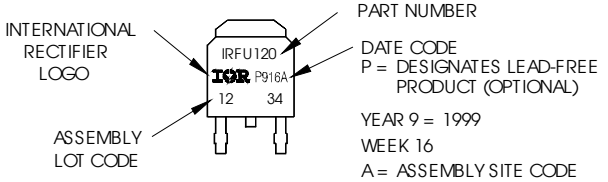
D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates "Lead-Free"

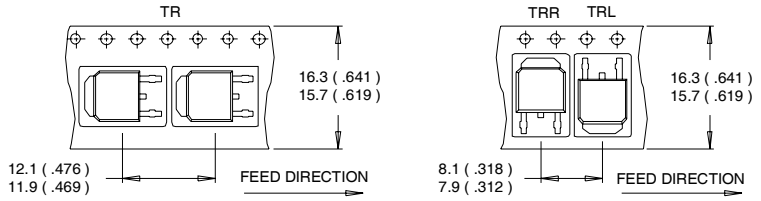


OR

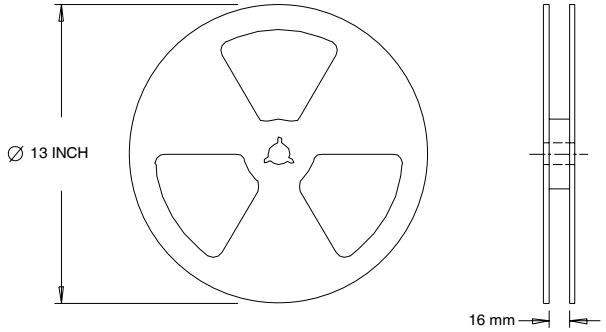


D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.45mH, R_G = 25Ω, I_{AS} = 30A, V_{GS} =10V. Part not recommended for use above this value.

③ $I_{SD} \leq$ 30A, di/dt ≤ 280A/μs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C.

④ Pulse width ≤ 1.0ms; duty cycle ≤ 2%.

⑤ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⑥ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.

⑦ This value determined from sample failure population. 100% tested to this value in production.

⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Automotive [Q101] market.

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